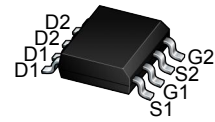


Description

The TX4884S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



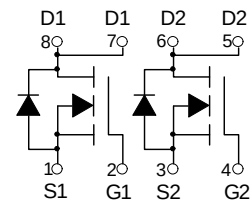
SOP-8

General Features

$V_{DS} = 40V$ $I_D = 12A$
 $R_{DS(ON)} < 16m\Omega$ @ $V_{GS}=10V$
 $R_{DS(ON)} < 24m\Omega$ @ $V_{GS}=4.5V$

Application

Battery protection
 Load switch
 Uninterruptible power supply



Dual N-Channel MOSFET

Absolute Maximum Ratings@ $T_J=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Drain Current, V_{GS} @ 4.5V ³	12	A
$I_D@T_A=70^\circ C$	Drain Current, V_{GS} @ 4.5V ³	7	A
I_{DM}	Pulsed Drain Current ¹	40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.9	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	65	$^\circ C/W$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=8A$	-	12.0	16	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	18.9	24	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=8A$	33	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	964	-	PF
Output Capacitance	C_{OSS}		-	109	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=2.5\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	5.5	-	nS
Turn-on Rise Time	t_r		-	14	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=8A,$ $V_{GS}=10V$	-	22.9	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	5.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=9A$	-	0.8	1.2	V

Typical Electrical and Thermal Characteristics (Curves)

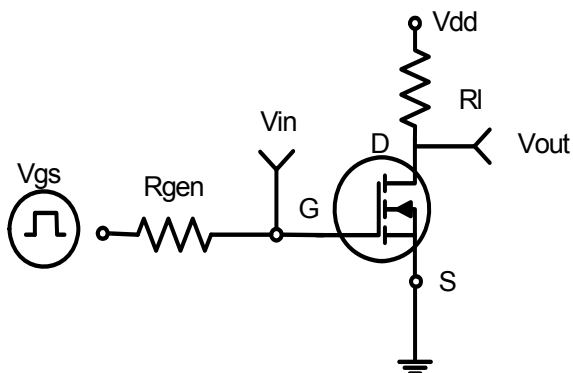


Figure 1: Switching Test Circuit

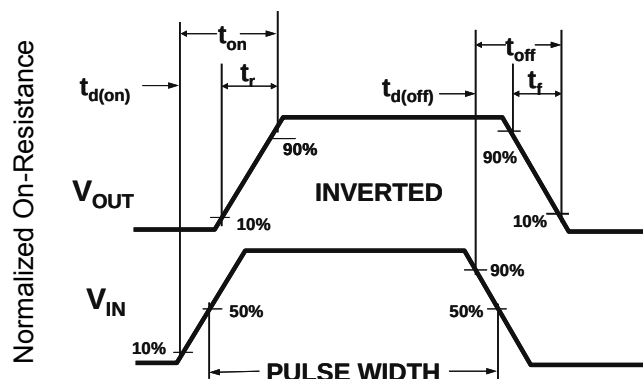


Figure 2: Switching Waveforms

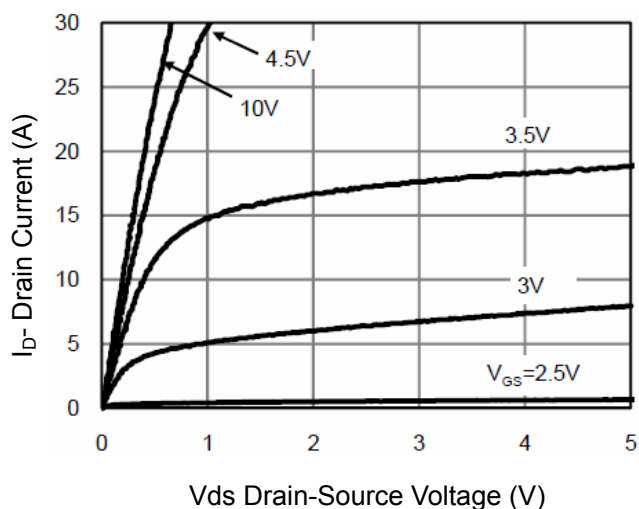


Figure 3 Output Characteristics

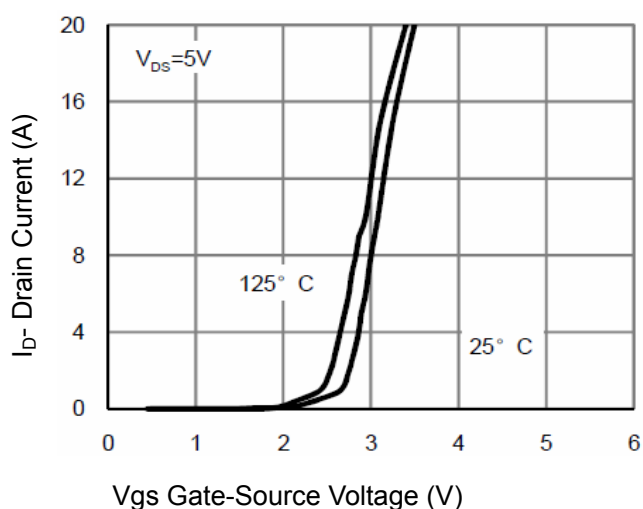


Figure 4 Transfer Characteristics

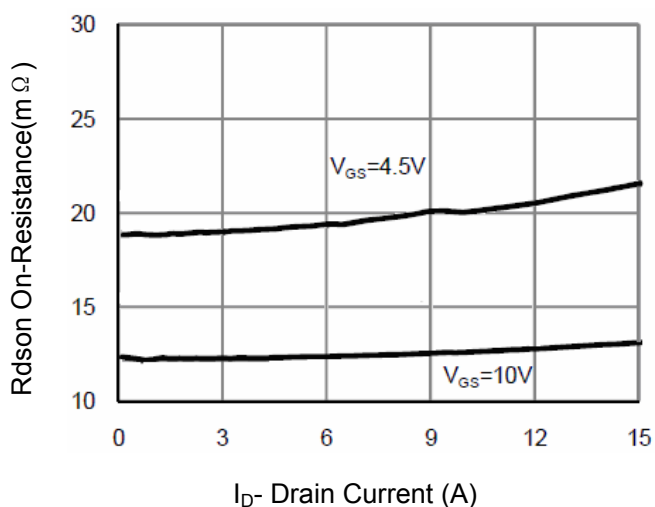


Figure 5 Drain-Source On-Resistance

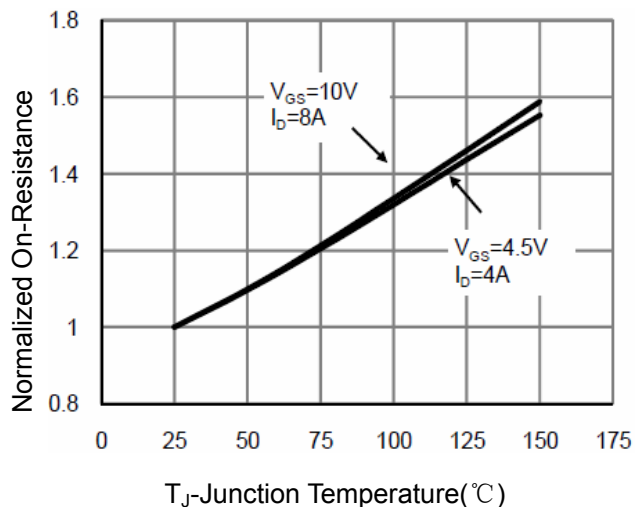
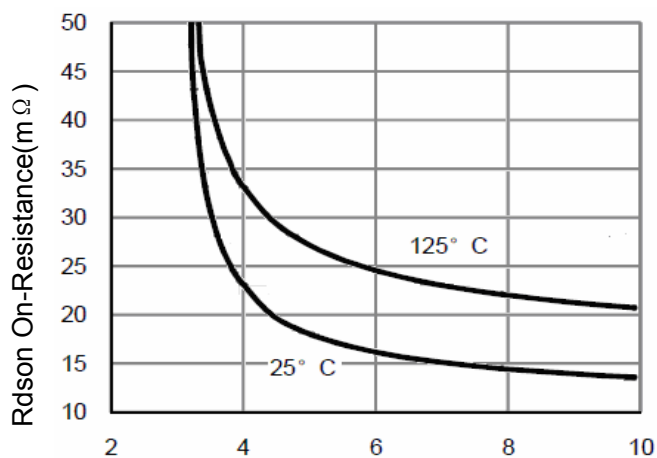
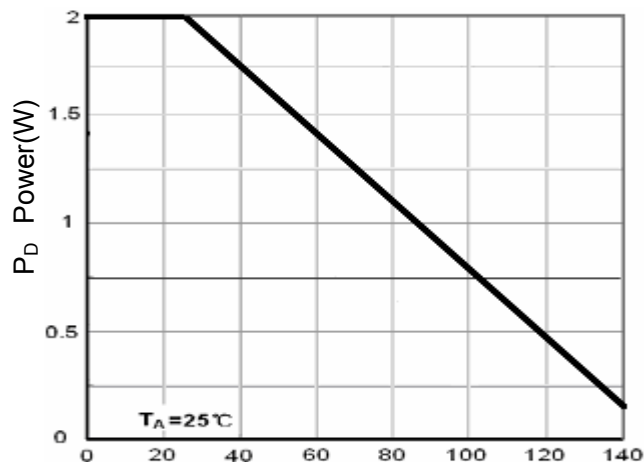


Figure 6 Drain-Source On-Resistance



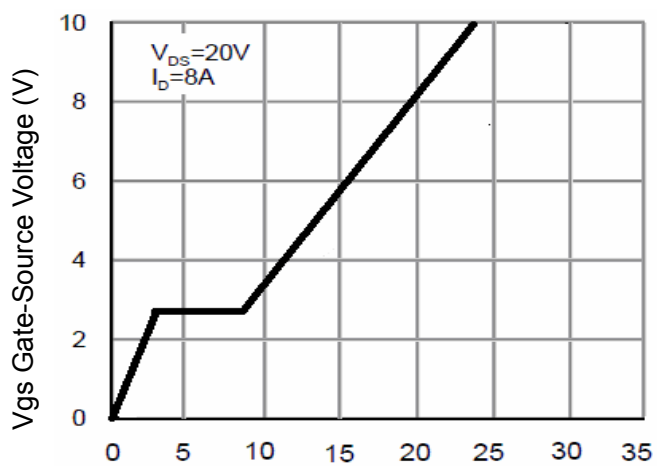
Vgs Gate-Source Voltage (V)

Figure 7 Rdson vs Vgs



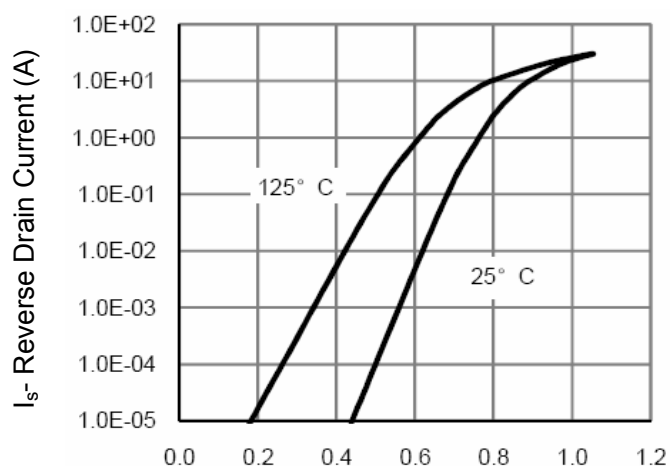
T_J-Junction Temperature (°C)

Figure 8 Power Dissipation



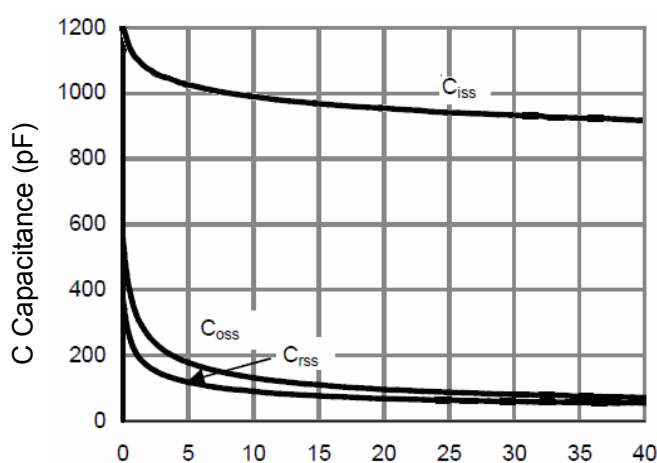
Qg Gate Charge (nC)

Figure 9 Gate Charge



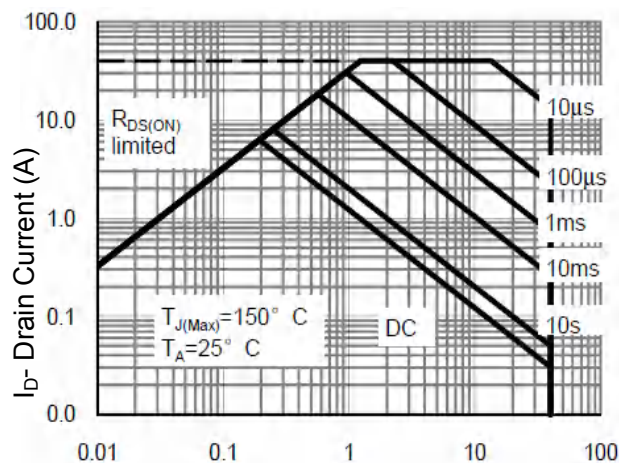
Vds Drain-Source Voltage (V)

Figure 10 Source-Drain Diode Forward



Vds Drain-Source Voltage (V)

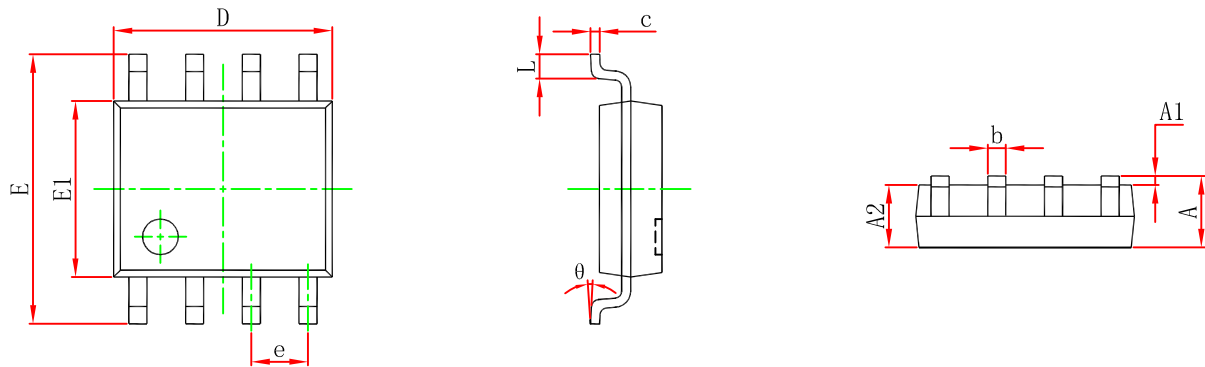
Figure 11 Capacitance vs Vds



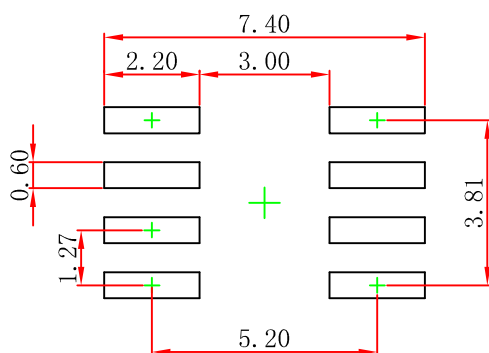
Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area

SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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